

DATA SHEET

PDTA143Z series

PNP resistor-equipped transistors;

R1 = 4.7 k Ω , R2 = 47 k Ω

Product data sheet
Supersedes data of 2003 Sep 08

2004 Aug 05

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PDTA143Z series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	–	–50	V
I _O	output current (DC)	–	–100	mA
R1	bias resistor	4.7	–	k Ω
R2	bias resistor	47	–	k Ω

DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT
	PHILIPS	EIAJ		
PDTA143ZE	SOT416	SC-75	37	PDTC143ZE
PDTA143ZEF	SOT490	SC-89	52	PDTC143ZEF
PDTA143ZK	SOT346	SC-59	19	PDTC143ZK
PDTA143ZM	SOT883	SC-101	DP	PDTC143ZM
PDTA143ZS	SOT54 (TO-92)	SC-43	TA143Z	PDTC143ZS
PDTA143ZT	SOT23	–	*19 ⁽¹⁾	PDTC143ZT
PDTA143ZU	SOT323	SC-70	*47 ⁽¹⁾	PDTC143ZU

Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTA143ZS		1 2 3	base collector emitter
PDTA143ZE PDTA143ZEF PDTA143ZK PDTA143ZT PDTA143ZU		1 2 3	base emitter collector
PDTA143ZM		1 2 3	base emitter collector

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	–	–50	V
V _{CEO}	collector-emitter voltage	open base	–	–50	V
V _{EBO}	emitter-base voltage	open collector	–	–10	V
V _I	input voltage				
		positive	–	+5	V
	negative		–	–30	V
I _O	output current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT23	note 1	–	250	mW
	SOT54	note 1	–	500	mW
	SOT323	note 1	–	200	mW
	SOT346	note 1	–	250	mW
	SOT416	note 1	–	150	mW
	SOT490	notes 1 and 2	–	250	mW
SOT883	notes 2 and 3	–	250	mW	
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air		
	SOT23	note 1	500	K/W
	SOT54	note 1	250	K/W
	SOT323	note 1	625	K/W
	SOT346	note 1	500	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
SOT883	notes 2 and 3	500	K/W	

Notes

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CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -30 V; I _B = 0	-	-	-1	μ A
		V _{CE} = -30 V; I _B = 0; T _j = 150 °C	-	-	-50	μ A
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0	-	-	-170	μ A
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -10 mA	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -5 mA; I _B = -0.25 mA	-	-	-100	mV
V _{i(off)}	input-off voltage	I _C = -100 μ A; V _{CE} = -5 V	-	-0.6	-0.5	V
V _{i(on)}	input-on voltage	I _C = -5 mA; V _{CE} = -0.3 V	-1.3	-0.9	-	V
R1	input resistor		3.3	4.7	6.1	k Ω
$\frac{R2}{R1}$	resistor ratio		8	10	12	
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = -10 V; f = 1 MHz	-	-	3	pF

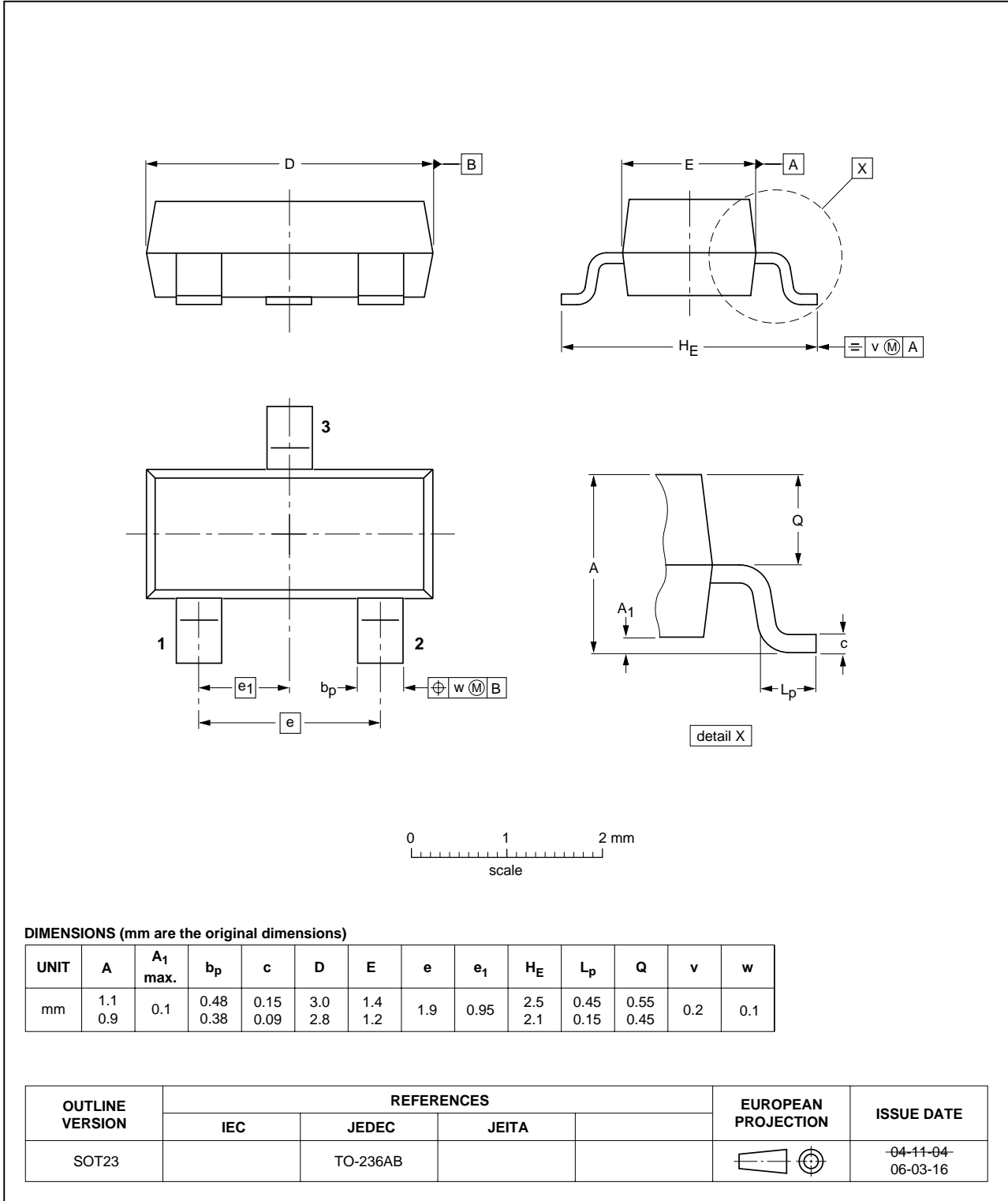
PNP resistor-equipped transistors;
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PACKAGE OUTLINES

Plastic surface-mounted package; 3 leads

SOT23

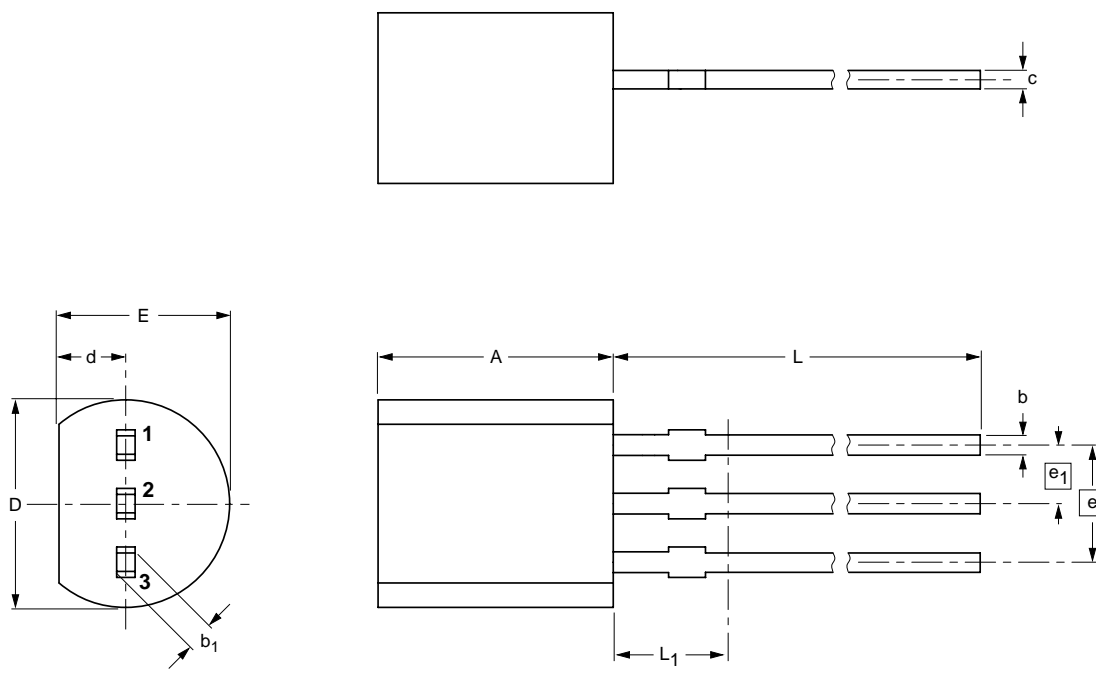


PNP resistor-equipped transistors;
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PDTA143Z series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

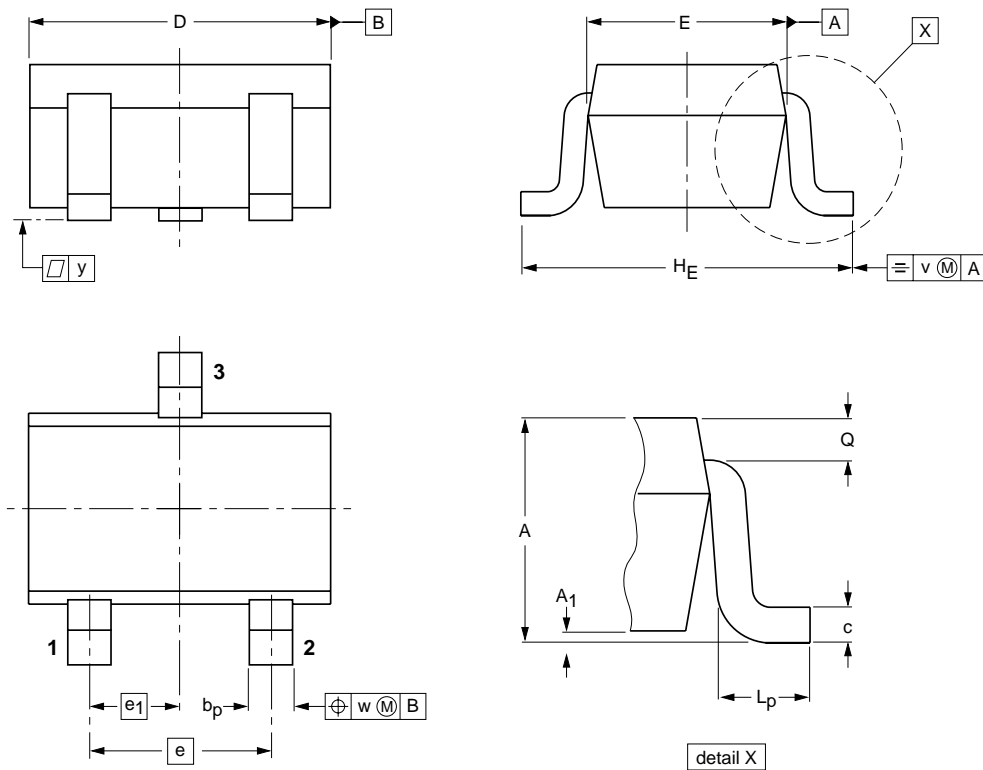
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	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		04-06-28 04-11-16

PNP resistor-equipped transistors;
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PDTA143Z series

Plastic surface-mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

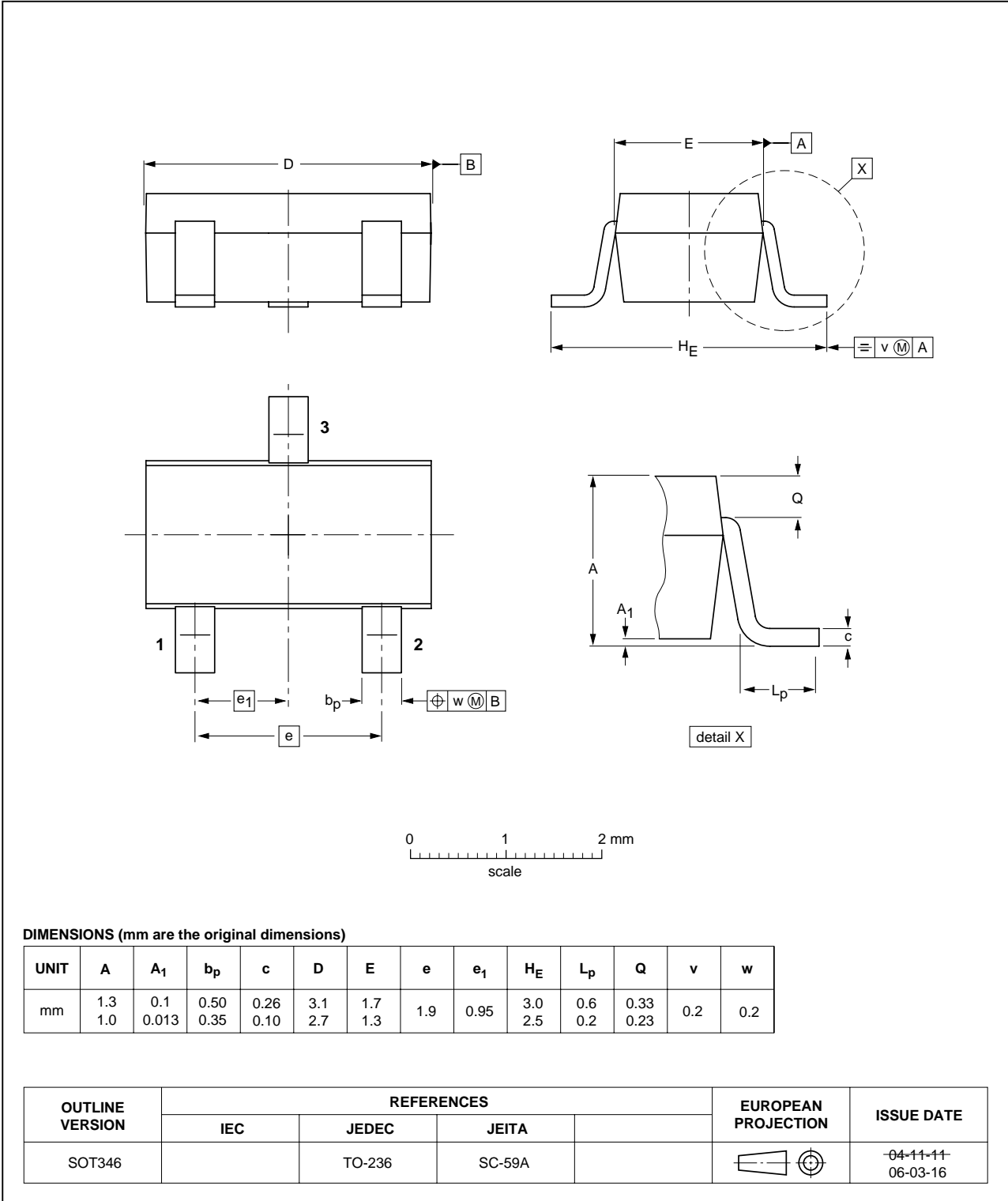
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT323			SC-70			04-11-04 06-03-16

PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = 47 kΩ

PDTA143Z series

Plastic surface-mounted package; 3 leads

SOT346

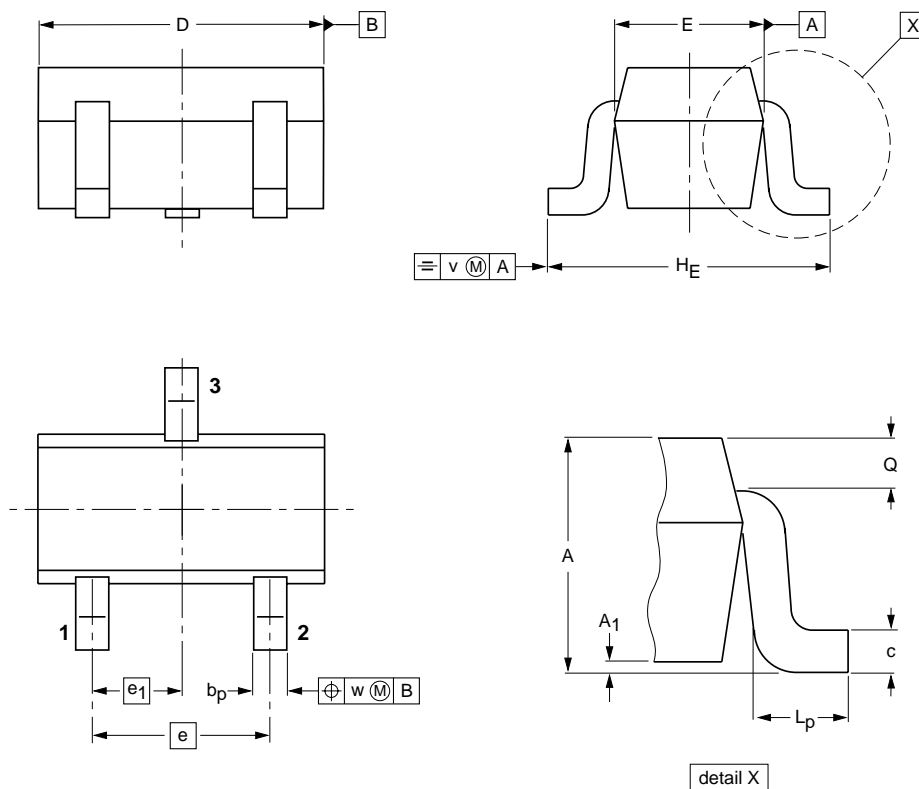


PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = 47 kΩ

PDTA143Z series

Plastic surface-mounted package; 3 leads

SOT416



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max	bp	c	D	E	e	e1	HE	Lp	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

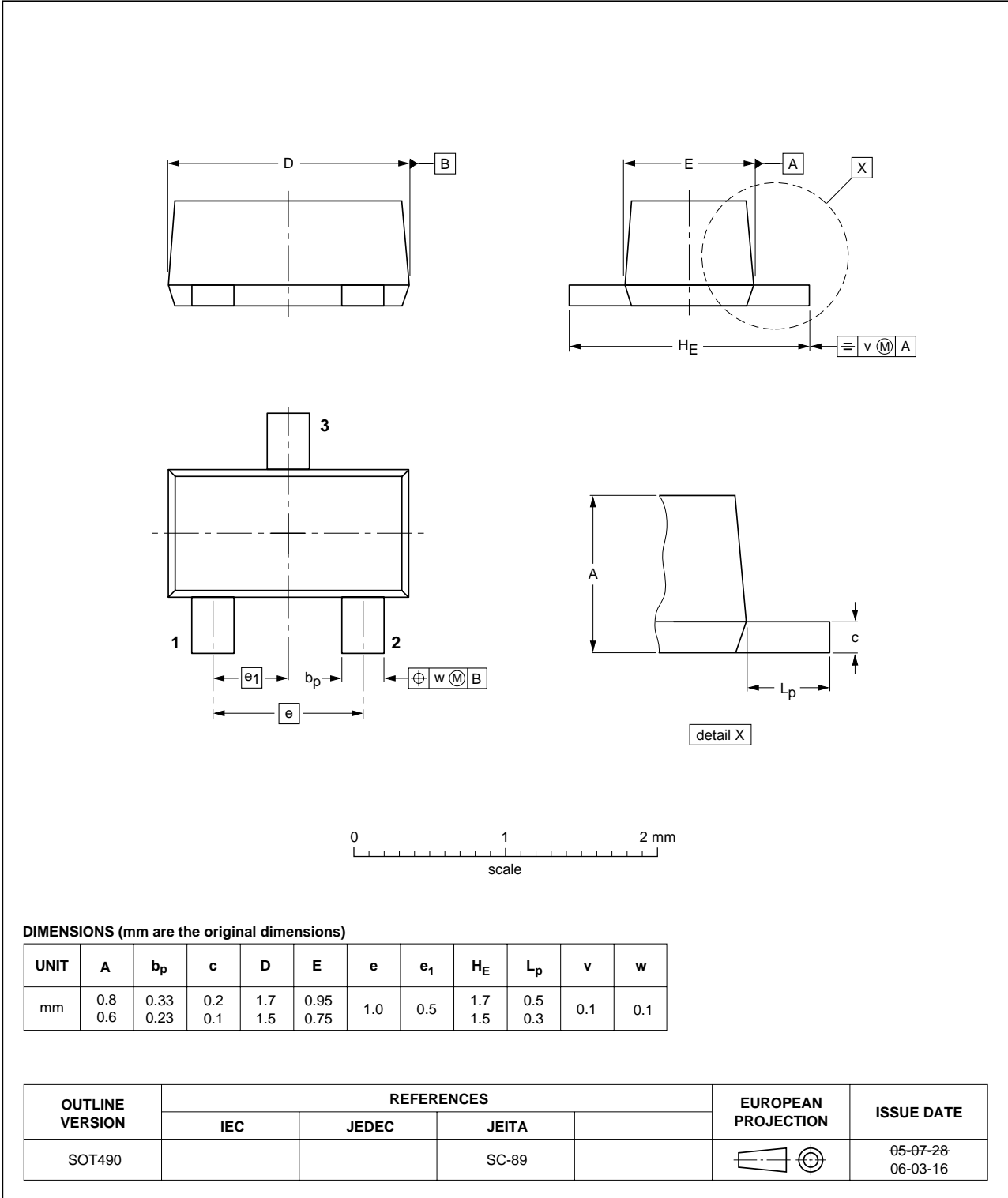
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	IEC	JEDEC	JEITA		
SOT416			SC-75		04-11-04 06-03-16

PNP resistor-equipped transistors;
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PDTA143Z series

Plastic surface-mounted package; 3 leads

SOT490

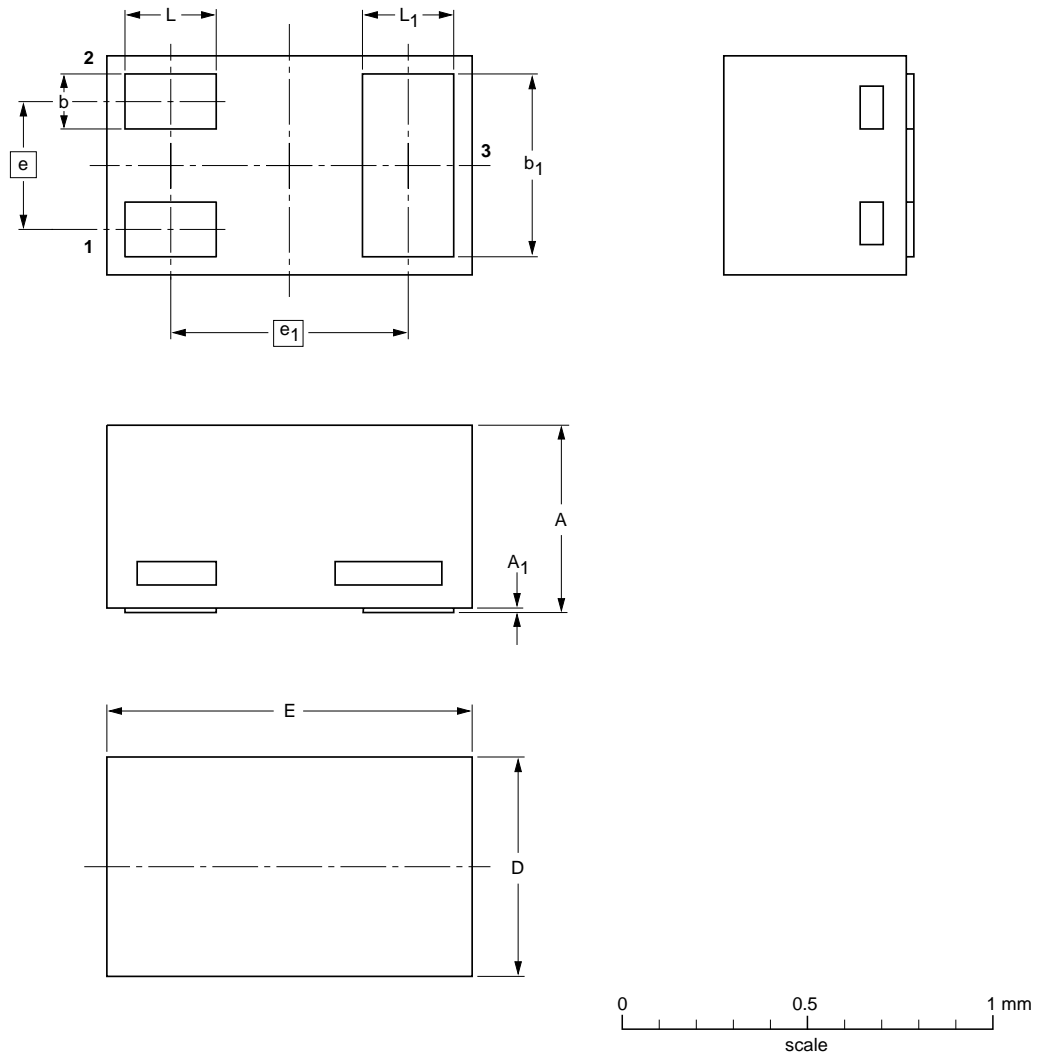


PNP resistor-equipped transistors;
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Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾	A ₁ max.	b	b ₁	D	E	e	e ₁	L	L ₁
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT883			SC-101		03-02-05 03-04-03

PNP resistor-equipped transistors;
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PDTA143Z series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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